

Silicon Diode

BYV27-600

600V/1.6A

DATASHEET

OEM – Philips

Source: Philips Databook 1999

Ultra fast low-loss controlled avalanche rectifiers

BYV27 series

FEATURES

- Glass passivated
- High maximum operating temperature
- Low leakage current
- Excellent stability
- Guaranteed avalanche energy absorption capability
- Available in ammo-pack.

DESCRIPTION

Rugged glass SOD57 package, using a high temperature alloyed construction.

This package is hermetically sealed and fatigue free as coefficients of expansion of all used parts are matched.

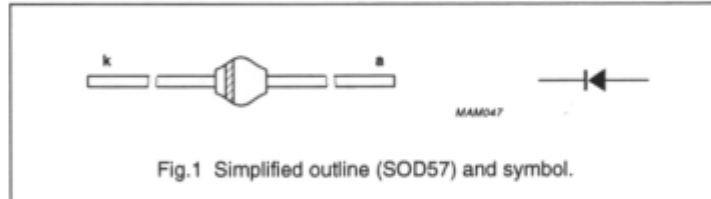


Fig.1 Simplified outline (SOD57) and symbol.

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{RRM}	repetitive peak reverse voltage				
	BYV27-50		–	50	V
	BYV27-100		–	100	V
	BYV27-150		–	150	V
	BYV27-200		–	200	V
	BYV27-300		–	300	V
	BYV27-400		–	400	V
	BYV27-500 BYV27-600		–	500 600	V
V_R	continuous reverse voltage				
	BYV27-50		–	50	V
	BYV27-100		–	100	V
	BYV27-150		–	150	V
	BYV27-200		–	200	V
	BYV27-300		–	300	V
	BYV27-400		–	400	V
	BYV27-500 BYV27-600		–	500 600	V
$I_{F(AV)}$	average forward current	$T_{ip} = 85\text{ °C}$; lead length = 10 mm; see Figs 2, 3 and 4;			
	BYV27-50 to 200	averaged over any 20 ms period;	–	2.0	A
	BYV27-300 and 400 BYV27-500 and 600	see also Figs 14, 15 and 16	–	1.9 1.6	A
$I_{F(AV)}$	average forward current	$T_{amb} = 60\text{ °C}$; printed-circuit board mounting (see Fig. 25);			
	BYV27-50 to 200	see Figs 5, 6 and 7;	–	1.30	A
	BYV27-300 and 400 BYV27-500 and 600	averaged over any 20 ms period; see also Figs 14, 15 and 16	–	1.25 1.10	A

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SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I_{FRM}	repetitive peak forward current	$T_{ip} = 85\text{ °C}$; see Figs 8, 9 and 10	-	20	A
	BYV27-50 to 400			16	A
I_{FRM}	repetitive peak forward current	$T_{amb} = 60\text{ °C}$; see Figs 11, 12 and 13	-	14	A
	BYV27-50 to 200			13	A
	BYV27-300 and 400 BYV27-500 and 600			11	A
I_{FSM}	non-repetitive peak forward current	$t = 10\text{ ms}$ half sine wave; $T_j = T_{jmax}$ prior to surge; $V_R = V_{RRMmax}$	-	50	A
	BYV27-50 to 400 BYV27-500 and 600			40	A
E_{RSM}	non-repetitive peak reverse avalanche energy	$L = 120\text{ mH}$; $T_j = T_{jmax}$ prior to surge; inductive load switched off	-	20	mJ
T_{stg}	storage temperature		-65	+175	°C
T_j	junction temperature	see Fig. 17	-65	+175	°C

ELECTRICAL CHARACTERISTICS $T_j = 25\text{ °C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT			
V_F	forward voltage	$I_F = 2\text{ A}$; $T_j = T_{jmax}$; see Figs 18, 19 and 20	-	-	0.78	V			
	BYV27-50 to 200				0.82	V			
	BYV27-300 and 400 BYV27-500 and 600				1.00	V			
V_F	forward voltage	$I_F = 2\text{ A}$; see Figs 18, 19 and 20	-	-	0.98	V			
	BYV27-50 to 200				1.05	V			
	BYV27-300 and 400 BYV27-500 and 600				1.25	V			
$V_{(BR)R}$	reverse avalanche breakdown voltage	$I_R = 0.1\text{ mA}$							
	BYV27-50					55	-	-	V
	BYV27-100					110	-	-	V
	BYV27-150					165	-	-	V
	BYV27-200					220	-	-	V
	BYV27-300					330	-	-	V
	BYV27-400					440	-	-	V
	BYV27-500					560	-	-	V
BYV27-600	675	-	-	V					
I_R	reverse current	$V_R = V_{RRMmax}$; see Fig. 21	-	-	5	μA			
		$V_R = V_{RRMmax}$; $T_j = 165\text{ °C}$; see Fig. 21	-	-	150	μA			

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SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
t_{rr}	reverse recovery time	when switched from $I_F = 0.5$ A to $I_R = 1$ A; measured at $I_R = 0.25$ A; see Fig. 27	-	-	25	ns
	BYV27-50 to 200				50	
C_d	diode capacitance	$f = 1$ MHz; $V_R = 0$; see Figs 22, 23 and 24	-	100	-	pF
	BYV27-50 to 200			80	-	pF
	BYV27-300 and 400			65	-	pF
$\left \frac{dI_R}{dt} \right $	maximum slope of reverse recovery current	when switched from $I_F = 1$ A to $V_R \geq 30$ V and $dI_F/dt = -1$ A/ μ s; see Fig. 26	-	-	4	A/ μ s

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-tp}$	thermal resistance from junction to tie-point	lead length = 10 mm	46	K/W
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 1	100	K/W

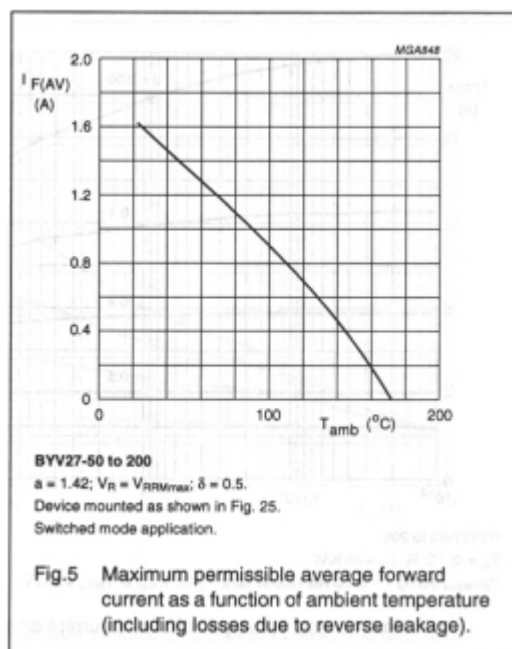
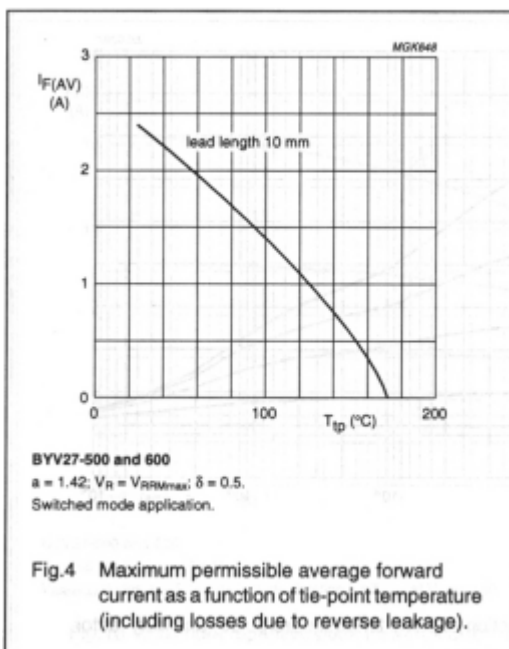
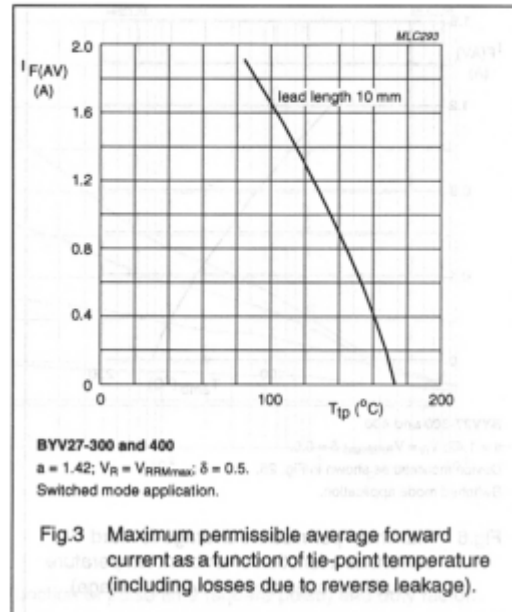
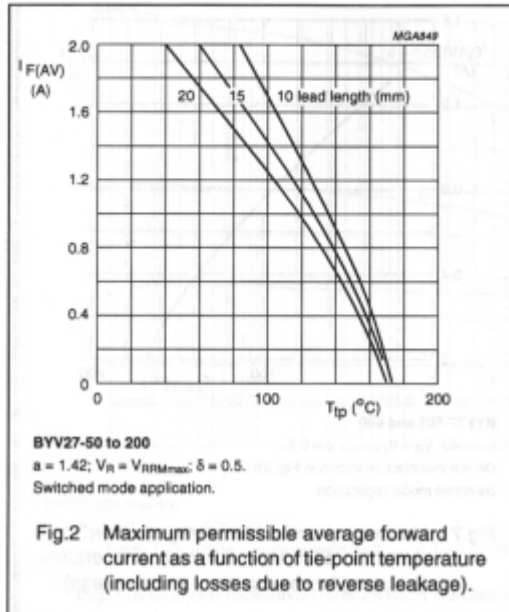
Note

1. Device mounted on an epoxy-glass printed-circuit board, 1.5 mm thick; thickness of Cu-layer ≥ 40 μ m, see Fig. 25. For more information please refer to the 'General Part of Handbook SC01'.

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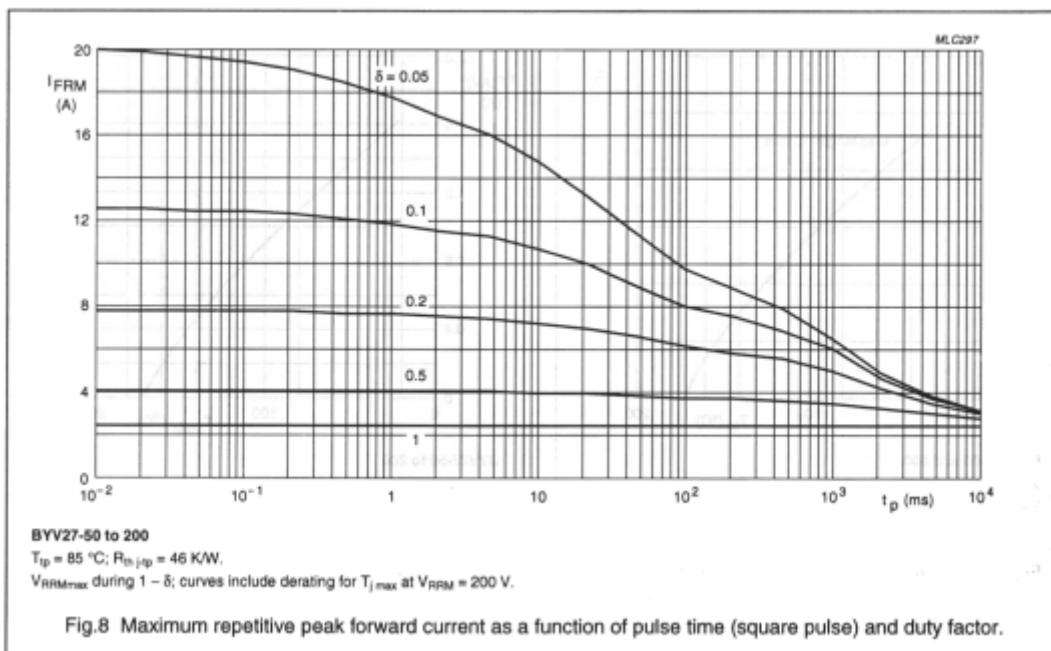
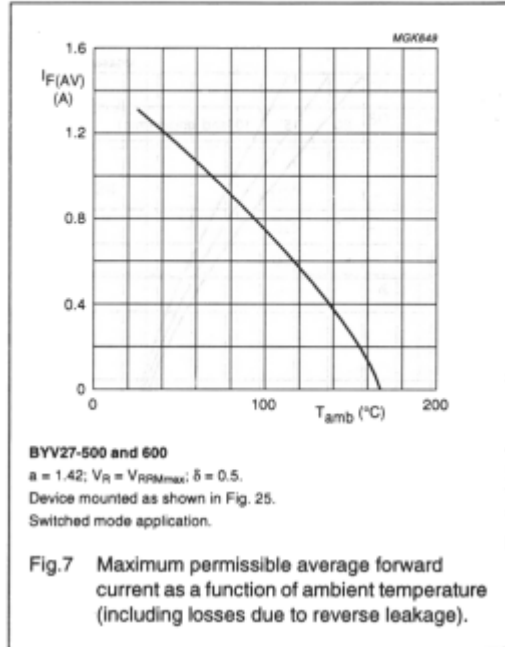
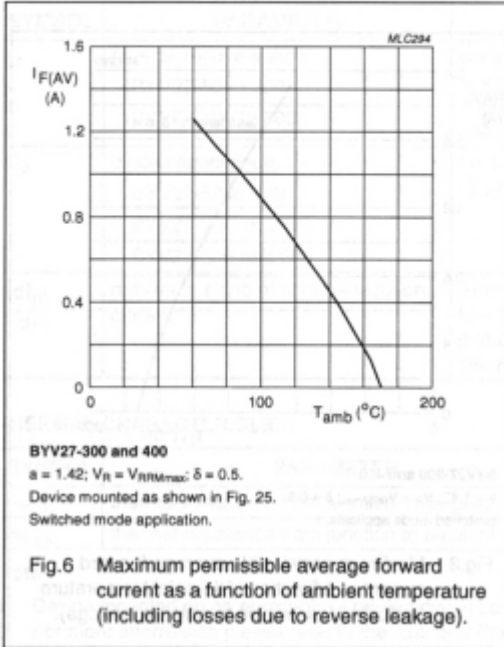
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GRAPHICAL DATA



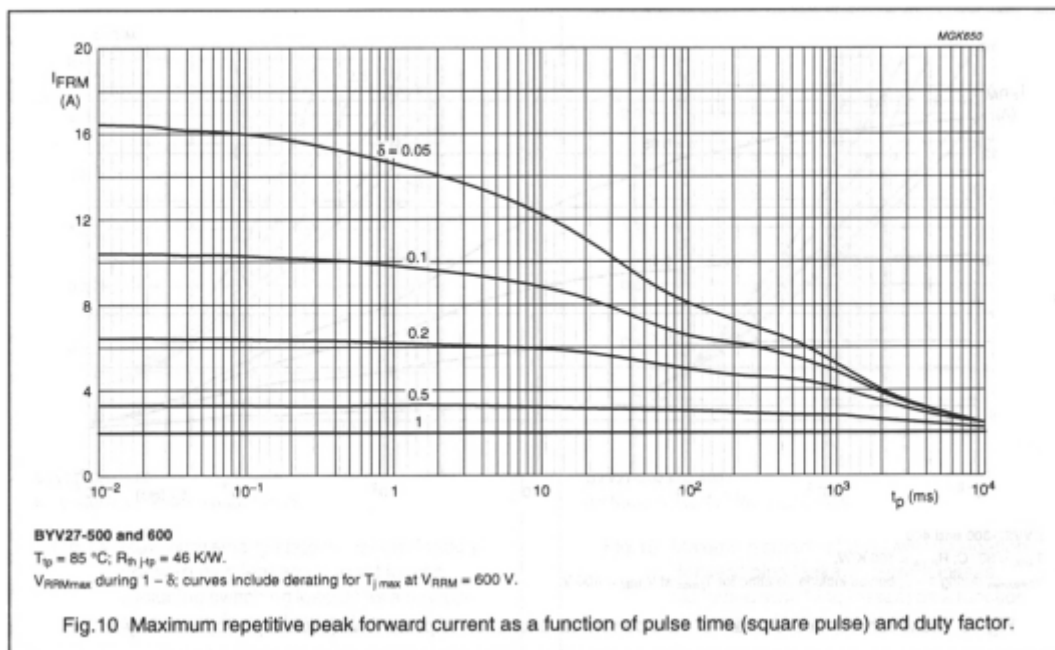
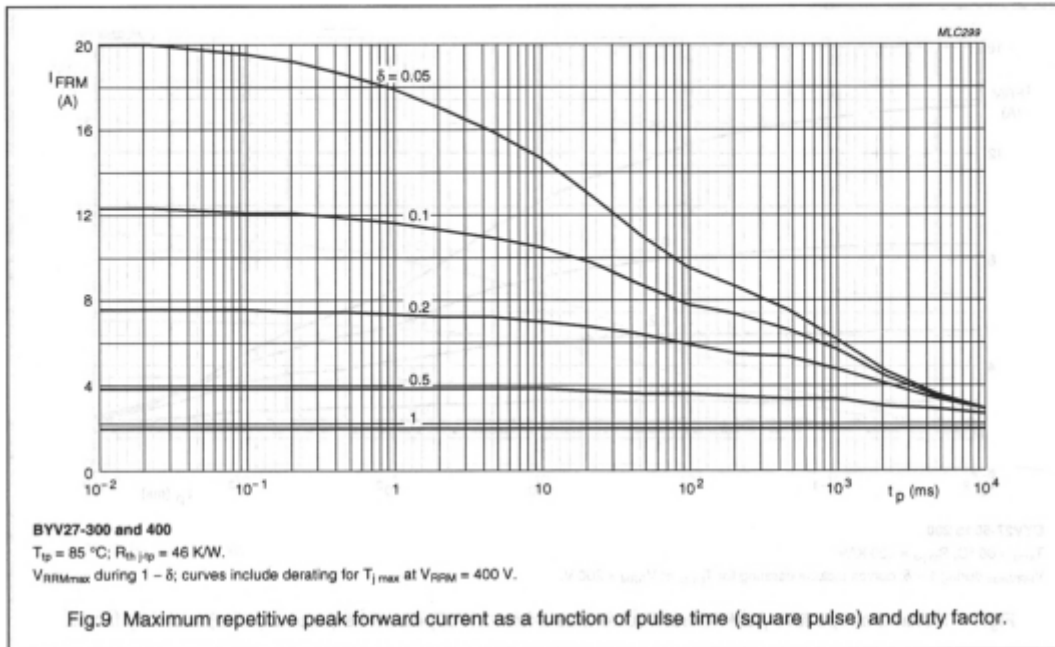
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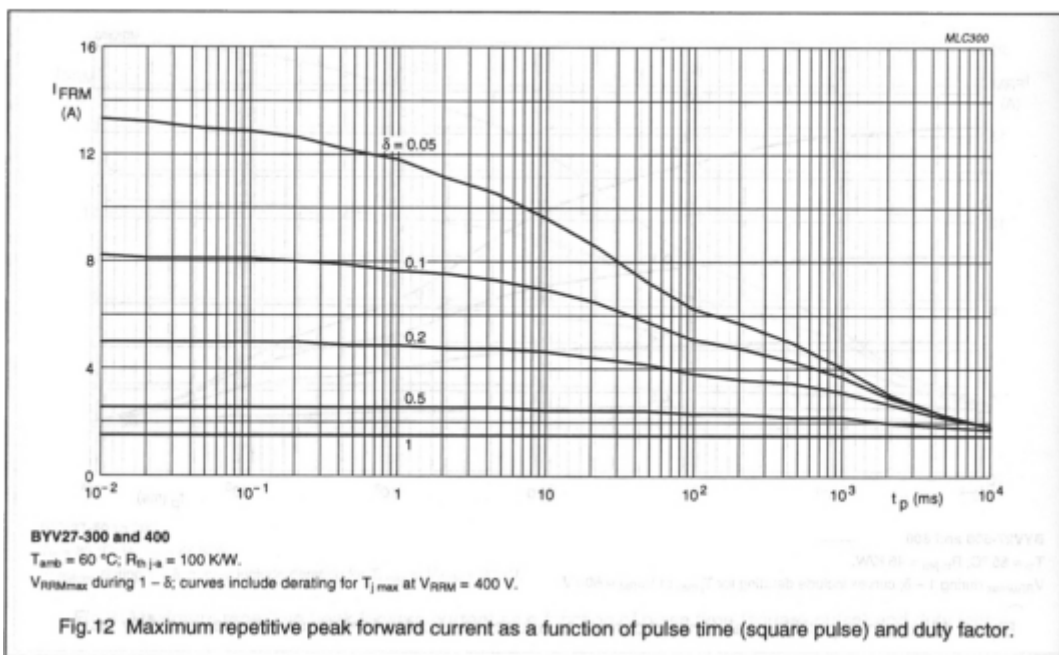
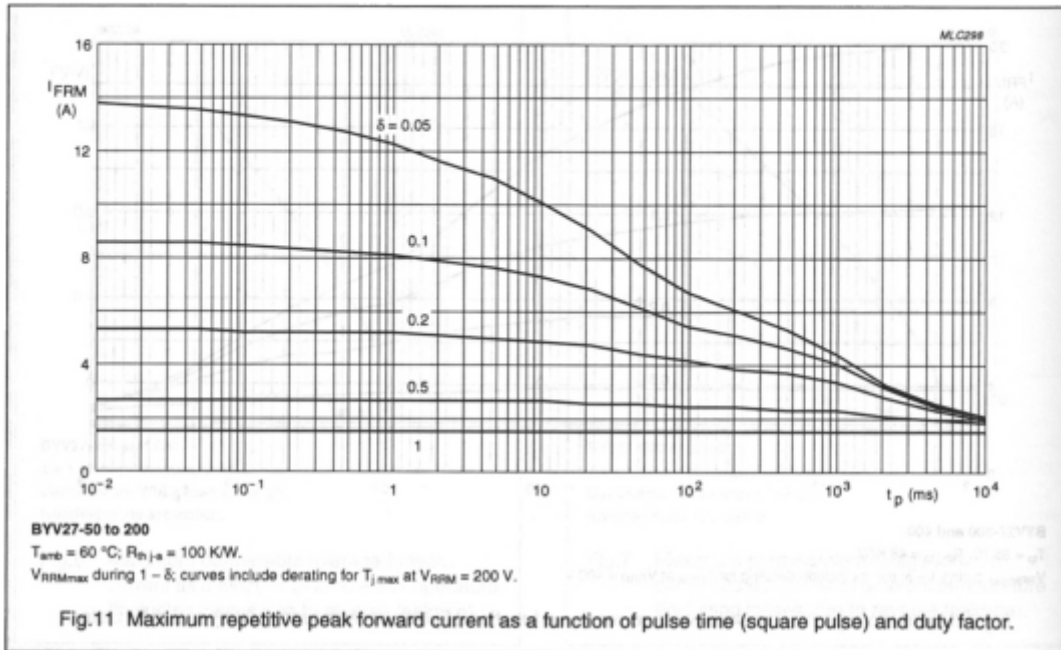
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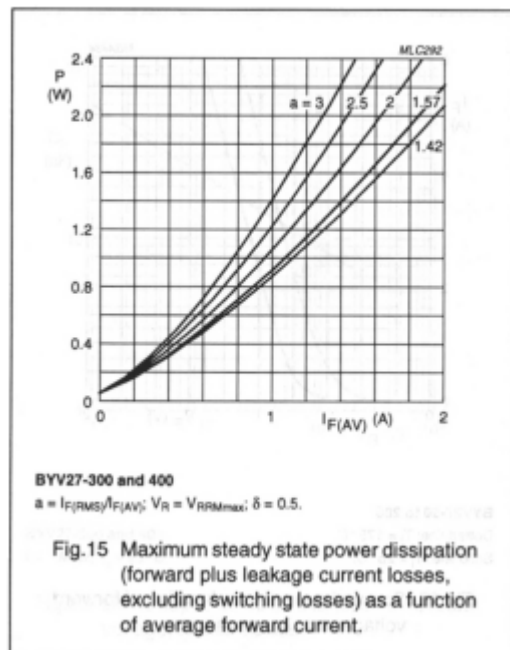
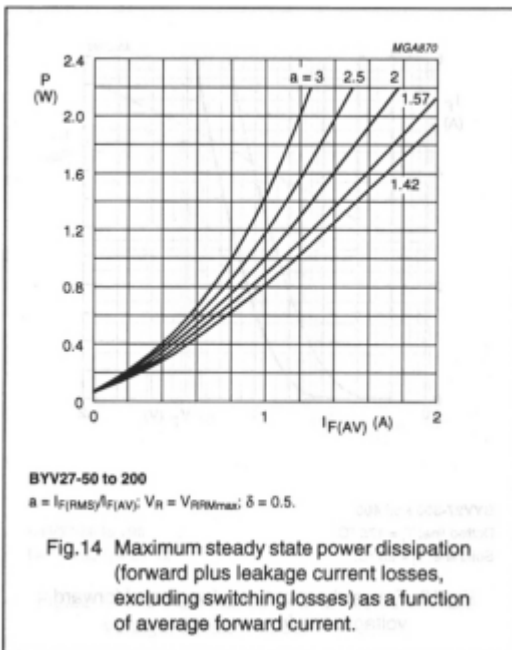
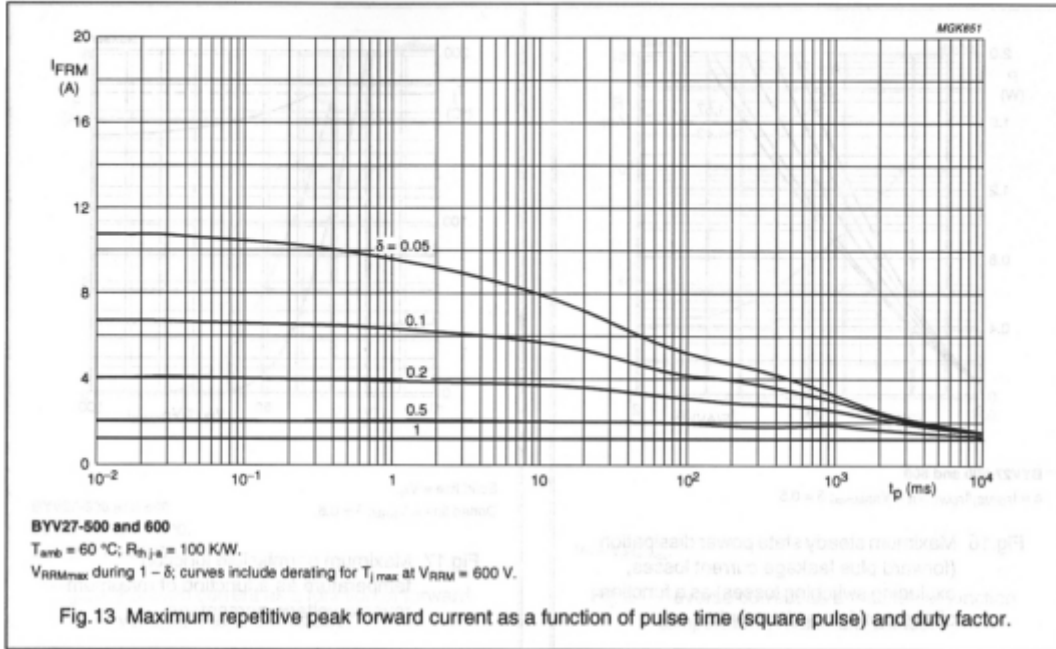
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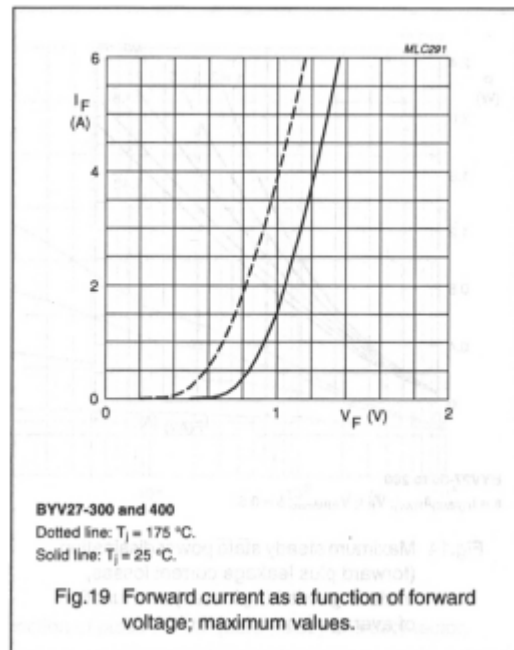
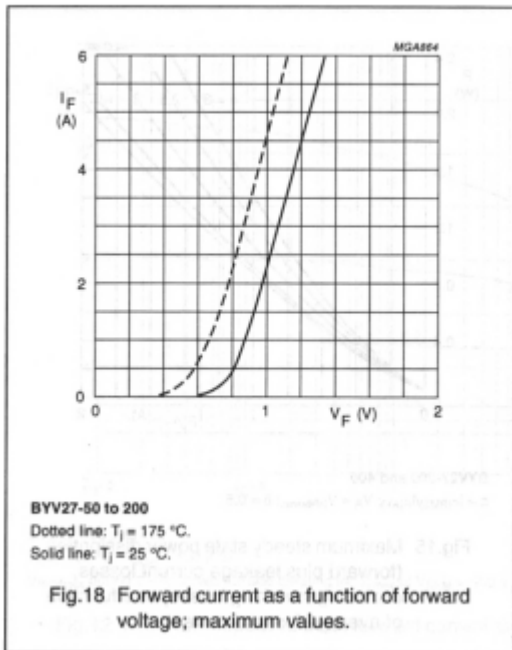
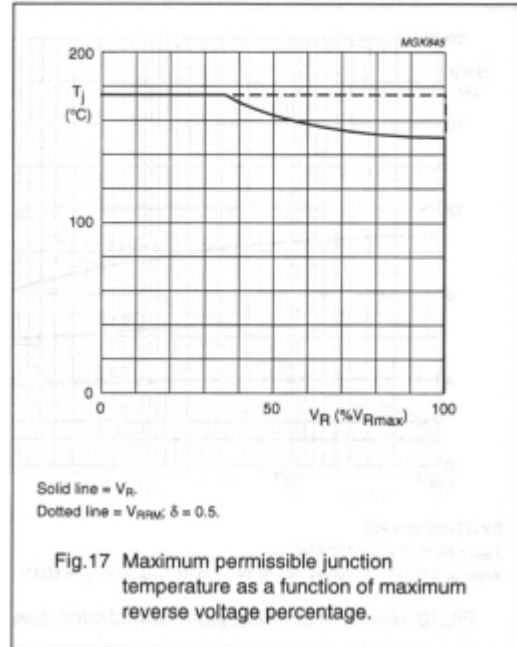
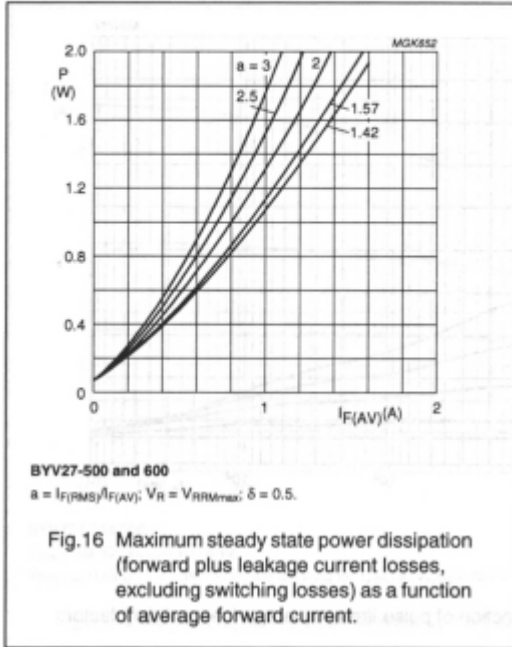
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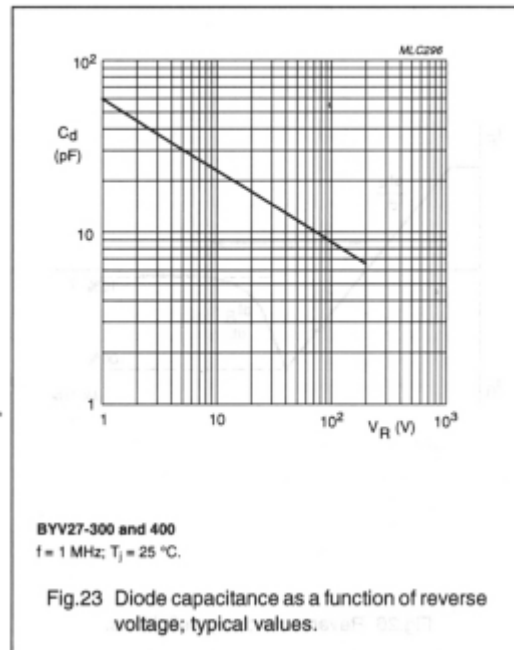
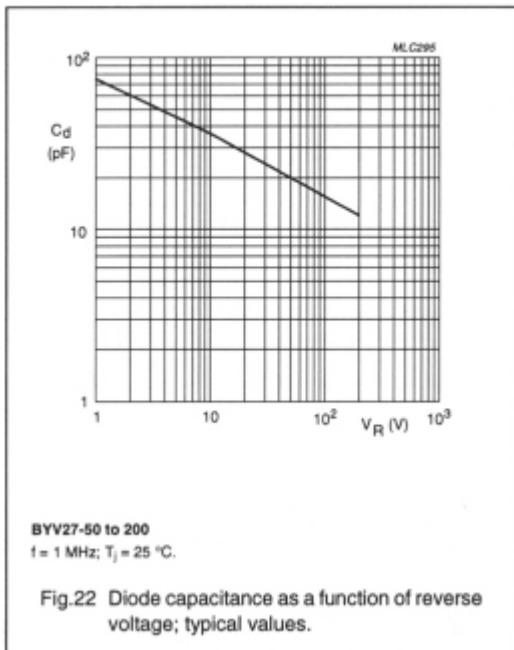
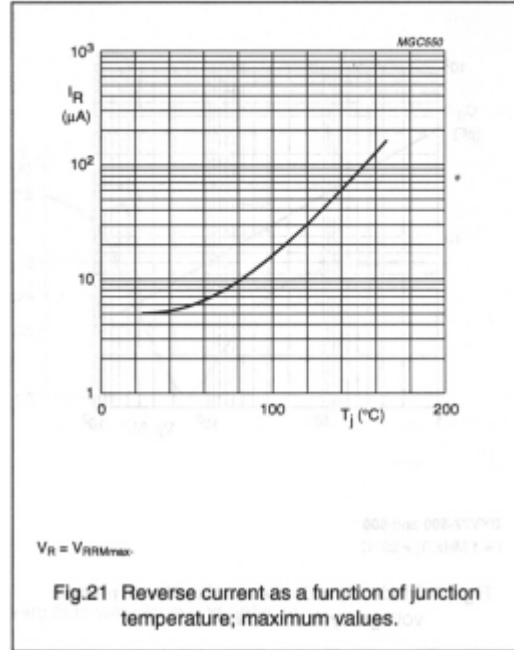
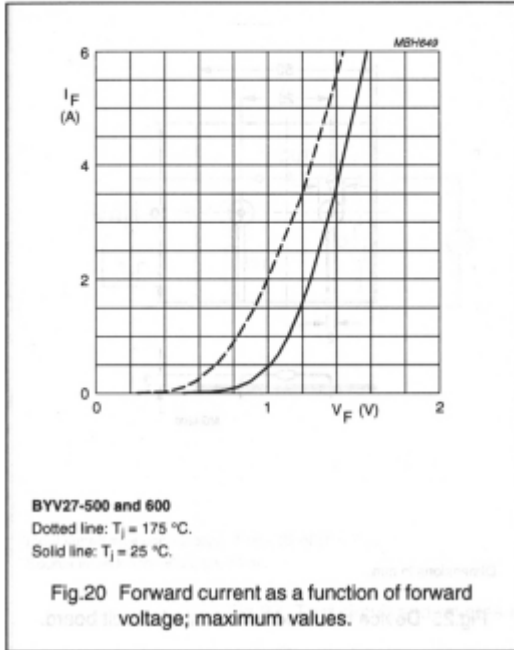
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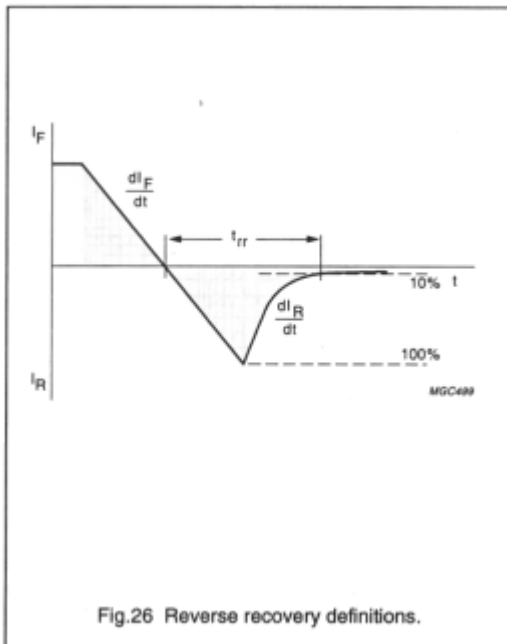
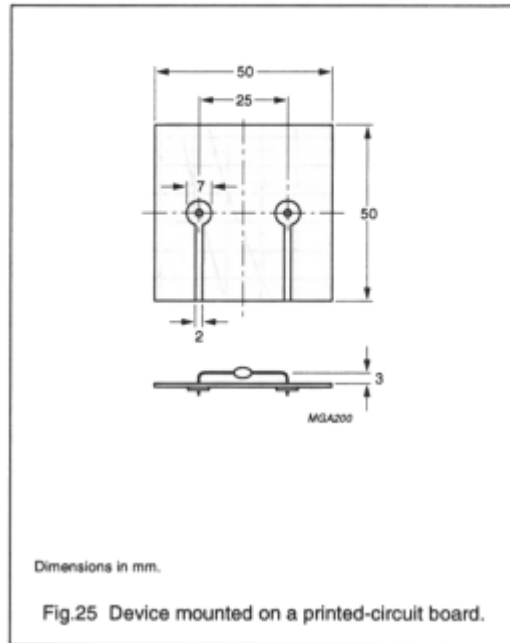
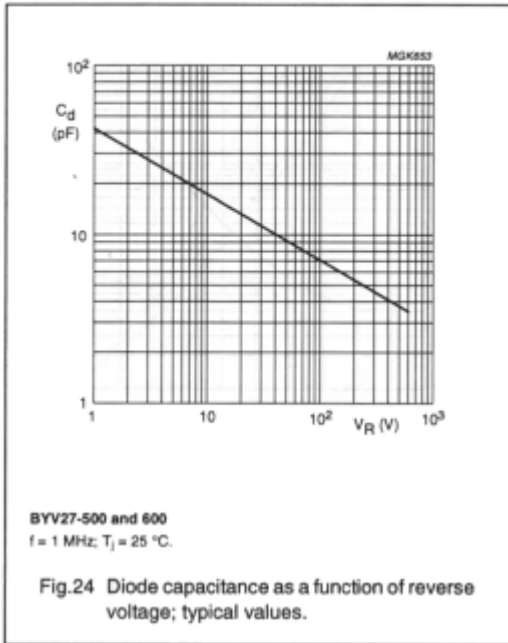
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